

# MJ10008-MJ10009

#### NPN SILICON POWER DARLINGTON TRANSISTORS

#### **FEATURES**

- Available as "HR" (high reliability) screened per MIL-PRF-19500, JANTX level. Add "HR" suffix to base part number.
- Available as non-RoHS (Sn/Pb plating), standard, and as RoHS by adding "-PBF" suffix.

#### **MAXIMUM RATINGS**

Rating	Symbol	MJ10008	MJ10009	Unit
Collector emitter voltage	V <sub>CEV</sub>	650	700	V
Collector emitter voltage	V <sub>CEX(sus)</sub>	450	500	V
Collector emitter voltage	V <sub>CEO(sus)</sub>	450	500	V
Emitter base voltage	V <sub>EBO</sub>	8.0		V
Collector current-Continuous	Ic	20		А
-Peak	Ісм	30		
Base current	I <sub>B</sub>	2.5		Α
Total power dissipation @ T <sub>C</sub> = 25°C		175		W
Total power dissipation @ T <sub>C</sub> = 100°C	$P_D$	100		W
Derate above 25°C		1.0		W/°C
Operating and storage temperature range	T <sub>J</sub> , T <sub>stg</sub>	-65 to +200		°C
Thermal resistance, junction to case	R <sub>eJC</sub>	1.0		°C/W

#### **ELECTRICAL CHARACTERISTICS** (T<sub>A</sub> = 25°C unless otherwise specified)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS	OFF CHARACTERISTICS				
Collector emitter sustaining voltage $(I_C = 100 \text{mA}, I_B = 0, V_{clamp} = \text{Rated } V_{CEO})$	MJ10008 MJ10009	V <sub>CEO(sus)</sub>	450 500	-	Vdc
Collector cutoff current ( $V_{CE}$ = Rated $V_{CEV}$ , $R_{BE}$ = 50 $\Omega$ , $T_{C}$ = 100°C)		I <sub>CER</sub>	-	5.0	mA
Collector cutoff current $(V_{CEV} = Rated\ V_{CEV},\ V_{BE(off)} = 1.5V)$ $(V_{CEV} = Rated\ V_{CEV},\ V_{BE(off)} = 1.5V,\ T_C = 150^{\circ}C)$		I <sub>CEV</sub>	-	0.25 5.0	mA
Emitter cutoff current $(V_{EB} = 2.0V, I_C = 0)$		I <sub>EBO</sub>	-	175	mA
ON CHARACTERISTICS (1)					
DC current gain $(I_C = 5.0A, V_{CE} = 5.0V)$ $(I_C = 10A, V_{CE} = 5.0V)$		h <sub>FE</sub>	40 30	400 300	-
Collector emitter saturation voltage $(I_C=10A,I_B=500mA)$ $(I_C=20A,I_B=2.0A)$ $(I_C=10A,I_B=500mA,T_C=100^{\circ}C)$		V <sub>CE(sat)</sub>	- -	2.0 3.5 2.5	٧
Base-emitter saturation voltage $(I_C=10A, I_B=500mA)$ $(I_C=10A, I_B=500mA, T_C=100^{\circ}C)$		V <sub>BE(sat)</sub>		2.5 2.5	V



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**ELECTRICAL CHARACTERISTICS** (T<sub>A</sub> = 25°C unless otherwise specified)

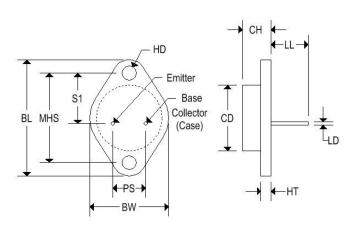
Characteristic		Symbol	Min	Max	Unit
Diode forward voltage (IF = 10A)		V <sub>f</sub>	-	5.0	V
DYNAMIC CHARACTERISTICS	DYNAMIC CHARACTERISTICS				
Small signal current gain <sup>(2)</sup> ( $I_C = 1.0A$ , $V_{CE} = 10V$ , $f_{test} = 1MHz$ )		h <sub>fe</sub>	8.0	-	-
Output capacitance ( $V_{CB} = 10V$ , $I_E = 0$ , $f_{test} = 100kHz$ )		Соь	100	-	pF
SWITCHING CHARACTERISTICS					
Delay time	$(V_{CC} = 250V, I_C = 5.0A,$ $I_{B1} = 500mA, V_{BE(off)} = 5.0V,$ $t_D = 50\mu s, duty cycle ≤ 2%)$	t <sub>d</sub>	-	0.25	μs
Rise time		tr	-	1.5	
Storage time		ts	-	2.0	
Fall time	- τ <sub>μ</sub> σομο, αατή εγείε ± 270/	t <sub>f</sub>	-	0.6	

Note 1: Pulse test: pulse width = 5ms, duty cycle ≤ 2%.

Note 2:  $f_T = |h_{fe}| * f_{test}$ 

#### **MECHANICAL CHARACTERISTICS**

Case	TO-3
Marking	Alpha-numeric
Polarity	See below

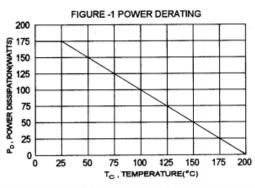


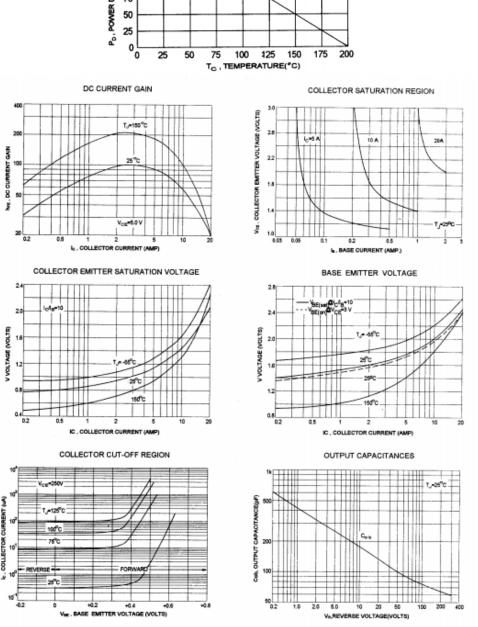
	TO-3			
	Inches		Millim	neters
	Min	Max	Min	Max
CD	-	0.875	1	22.220
CH	0.250	0.380	6.860	9.650
HT	0.060	0.135	1.520	3.430
BW	-	1.050	-	26.670
HD	0.131	0.188	3.330	4.780
LD	0.038	0.043	0.970	1.090
LL	0.312	0.500	7.920	12.700
BL	1.550	REF	39.370 REF	
MHS	1.177	1.197	29.900	30.400
PS	0.420	0.440	10.670	11.180
<b>S</b> 1	0.655	0.675	16.640	17.150



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